

WHAT IS CLAIMED IS:

1. An image sensor, comprising:

a voltage boosting circuit, which produces a boosted reset voltage on a reset line at a higher level than a power supply output level; and

a voltage protection circuit, which is connected to said reset line, and which protects at least one transistor against being forward biased by said boosted reset voltage.

2. An image sensor as in claim 1, wherein said voltage protection circuit includes at least one additional transistor of a type which can not be forward biased by said boosted reset voltage.

3. An image sensor as in claim 1, wherein said voltage boosting circuit includes a first capacitor, and first and second switching elements, which is first precharged at one plate by said first switching element, and subsequently isolated at said one plate by said second switching element, and biased at the other plate to produce an output voltage which is increased to a boosted voltage related to an amount of said bias added to an amount of said

precharge.

4. An image sensor as in claim 3, wherein said second switching element is one which is not forward biased by a voltage that is greater than the power supply voltage.

5. An image sensor as in claim 4, wherein said second switching element is an N type switching transistor.

6. An image sensor as in claim 4, wherein said second switching element includes first and second series connected switching transistors.

7. An image sensor as in claim 1, further comprising an output switch, which is capable of isolating against a voltage higher than a supply voltage, which is selectively turned on and off based on a level of boosting.

8. An image sensor as in claim 7, wherein said output switch further comprises a first passing transistor and a second shorting transistor, said first passing transistor in series between said boosted reset voltage and an output line, and said second shorting transistor connected between said output line and ground.

9. An image sensor as in claim 8, wherein said first passing transistor is an NMOS type passing transistor, and said shorting transistor is a PMOS type shorting transistor.

10. An image sensor as in claim 3, further comprising a second capacitor, charged to a different voltage than said first capacitor, to produce a second boosted output.

11. An image sensor as in claim 10, wherein one end of each of said first and second capacitors are charged by the same switch.

12. An image sensor as in claim 1, further comprising a row driver circuitry, which uses a first line as a row select, and a second line, intended for row select of a different row than a currently selected row, for a reset line.

13. An image sensor as in claim 11, further comprising a row driver circuitry, which uses a first line as a row select, and a second line, intended for row select of a different row than a currently selected row, for a reset

line.

14. A method, comprising:

carrying out an operation to increase a level of an output reset signal to a boosted level, which is greater than a power supply voltage; and

using a switching circuit to isolate said reset signal from at least the power supply voltage, which switching circuit can withstand a voltage higher than said power supply voltage.

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